

# Alain Portavoce

## List of Publications by Year in descending order

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36  
papers

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citations

1478280

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1199470

12  
g-index

38  
all docs

38  
docs citations

38  
times ranked

191  
citing authors

#	ARTICLE	IF	CITATIONS
1	Phase transitions in thermoelectric Mg-Ag-Sb thin films. Journal of Alloys and Compounds, 2022, 900, 163534.	2.8	4
2	Kinetic Monte Carlo simulations of GeSbTe thin film crystallization. Nanotechnology, 2022, 33, 295601.	1.3	3
3	Seebeck coefficient in multiphase thin films. Materials Letters, 2020, 266, 127460.	1.3	6
4	Coupling Secondary Ion Mass Spectrometry and Atom Probe Tomography for Atomic Diffusion and Segregation Measurements. Microscopy and Microanalysis, 2019, 25, 517-523.	0.2	2
5	Role of Atomic Transport Kinetic on Nano-Film Solid State Growth. , 2018, 17, 115-146.		0
6	Diffusion Measurements in Nanostructures. , 2017, , 1-35.		0
7	Structural and Composition Effects on Electronic and Magnetic Properties in Thermoelectric $Mn_{1-x}Co_{1+y}Ge$ Materials. Journal of Physical Chemistry C, 2017, 121, 26575-26586.	1.5	11
8	First stages of Ni reaction with the Si(Ge) alloy. Journal of Alloys and Compounds, 2017, 695, 2799-2811.	2.8	3
9	Thermal stability of PdGe films on Ge(100) substrate. Scripta Materialia, 2016, 120, 45-48.	2.6	4
10	Atomic Transport in Nano-Crystalline Thin Films. Defect and Diffusion Forum, 2016, 367, 140-148.	0.4	3
11	Nanoporous Ge thin film production combining Ge sputtering and dopant implantation. Beilstein Journal of Nanotechnology, 2015, 6, 336-342.	1.5	7
12	Mn Diffusion and Reactive Diffusion in Ge: Spintronic Applications. Defect and Diffusion Forum, 2015, 363, 56-61.	0.4	3
13	Mechanism of $\hat{I}^2$ -FeSi <sub>2</sub> precipitates growth-and-dissolution and pyramidal defects' formation during oxidation of Fe-contaminated silicon wafers. Journal of Applied Physics, 2015, 117, .	1.1	6
14	Atomic redistribution of implanted Fe and associated defects around moving SiO <sub>2</sub> /Si interfaces. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 1166-1169.	0.8	0
15	Si/Ge intermixing during Ge Stranski-Krastanov growth. Beilstein Journal of Nanotechnology, 2014, 5, 2374-2382.	1.5	9
16	Direct observation of Ni decorated dislocation loops within As+-implanted silicon and arsenic clustering in Ni silicide contact. Microelectronic Engineering, 2013, 107, 184-189.	1.1	11
17	Dopant diffusivity and solubility in nickel silicides. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 670-673.	0.8	4
18	Three-dimensional composition mapping of NiSi phase distribution and Pt diffusion via grain boundaries in Ni <sub>2</sub> Si. Scripta Materialia, 2010, 62, 568-571.	2.6	54

#	ARTICLE	IF	CITATIONS
19	Simultaneous Measurements of Lattice and Grain Boundary Diffusion Coefficients via 2-Dimensional Simulations. Defect and Diffusion Forum, 2010, 297-301, 978-983.	0.4	0
20	Transition from anomalous kinetics toward Fickian diffusion for Si dissolution into amorphous Ge. Applied Physics Letters, 2008, 92, .	1.5	23
21	Dopant Diffusion during Amorphous Silicon Crystallization. Defect and Diffusion Forum, 2007, 264, 33-38.	0.4	10
22	Determination of Grain Boundary Diffusion Coefficients in C-Regime by Hwang-Balluffi Method: Silver Diffusion in Pd. Defect and Diffusion Forum, 0, 289-292, 763-767.	0.4	4
23	Unusual Behaviour of the Dissolutions Kinetics of one Monolayer of Si in Cu(001). Defect and Diffusion Forum, 0, 289-292, 601-606.	0.4	5
24	Atom Redistribution during co-Doped Amorphous Silicon Crystallization. Defect and Diffusion Forum, 0, 289-292, 329-337.	0.4	7
25	Thin Film Dissolution into Semi-Infinite Substrates: Surprising Interface Kinetics and Dissolution Modes. Defect and Diffusion Forum, 0, 289-292, 573-585.	0.4	0
26	Kinetic of Formation of Ni and Pd Silicides: Determination of Interfacial Mobility and Interdiffusion Coefficient by $\text{In Situ}$ Techniques. Solid State Phenomena, 0, 172-174, 640-645.	0.3	6
27	Numerical Simulation Support for Diffusion Coefficient Measurements in Polycrystalline Thin Films. Defect and Diffusion Forum, 0, 309-310, 63-72.	0.4	5
28	Sequential Phase Formation during Reactive Diffusion of a Nanometric-Thick Mn Film on Ge(111). Solid State Phenomena, 0, 172-174, 579-584.	0.3	5
29	Theoretical and Experimental Evidences of Sequential Phase Formation during Sub-Nanometric-Thick Film Reactive Diffusion. Solid State Phenomena, 0, 172-174, 633-639.	0.3	0
30	Nanometric-Size Effect upon Diffusion and Reaction in Semiconductors: Experimental and Theoretical Investigations. Defect and Diffusion Forum, 0, 323-325, 433-438.	0.4	0
31	Original Methods for Diffusion Measurements in Polycrystalline Thin Films. Defect and Diffusion Forum, 0, 322, 129-150.	0.4	12
32	Effect of Mn Thickness on the Mn-Ge Phase Formation during Reactions of 50 nm and 210 nm Thick Mn Films Deposited on Ge (111) Substrate. Defect and Diffusion Forum, 0, 323-325, 439-444.	0.4	2
33	Diffusion and Redistribution of Boron in Nickel Silicides. Defect and Diffusion Forum, 0, 323-325, 415-420.	0.4	6
34	Reactive Diffusion of Thin Si Deposits into Ni (111). Defect and Diffusion Forum, 0, 323-325, 421-426.	0.4	0
35	Atomic Transport in Nano-Crystalline Silicides Studied by $\text{In Situ}$ Auger Electron Spectroscopy: Interfacial Reaction Effect. Defect and Diffusion Forum, 0, 363, 12-20.	0.4	0
36	Redistribution of Metallic Impurities in Si during Annealing and Oxidation: W and Fe. Defect and Diffusion Forum, 0, 383, 17-22.	0.4	0